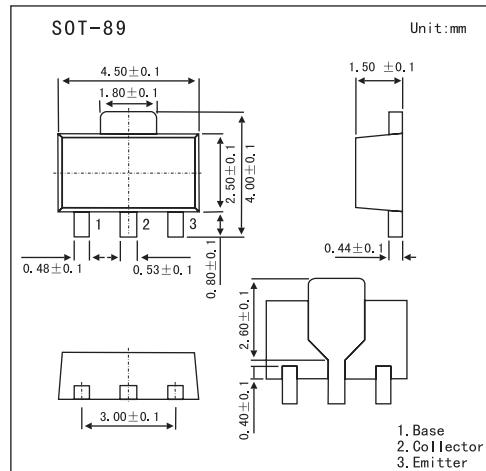


Power Transistor

2SD1898

■ Features

- High V_{CBO}, V_{CBO}=80V .
- High I_c, I_c=1A (DC) .
- Good h_{FE} linearity .
- Low V_{CE(sat)} .



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	120	V
Collector-emitter voltage	V _{CEO}	80	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _c	1	A
	I _c (Pulse) * ¹	2	A
Collector power dissipation	P _c	0.5	W
	P _c * ²	2	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

*1. Pw=20ms.

*2. 40X40X0.7mm Ceramic board.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base voltage	BV _{CBO}	I _c =50μA	120			V
Collector-emitter voltage	BV _{CEO}	I _c =1mA	80			V
Emitter-base voltage	BV _{EBO}	I _e =50μA	5			V
Collector cutoff current	I _{cbo}	V _{CB} =100V			1	μA
Emitter cutoff current	I _{ebo}	V _{EB} =4V			1	μA
Forward current transfer ratio	h _{FE}	V _{CE} =3V, I _c =0.5A	82		390	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =500mA, I _b =20mA		0.15	0.4	V
Transition frequency	f _T	V _{CE} =10V, I _e = -50mA, f=100MHz		100		MHz
Output capacitance	C _{ob}	V _{CB} =10V, I _e =0A, f=1MHz		20		pF

■ h_{FE} Classification

Marking	DF		
	P	Q	R
h _{FE}	82~180	120~270	180~390